

600V 0.6Ω Super Junction Power MOSFET

Description

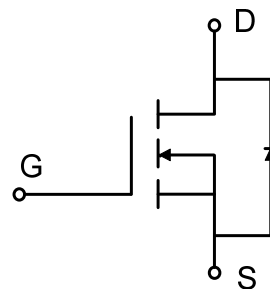
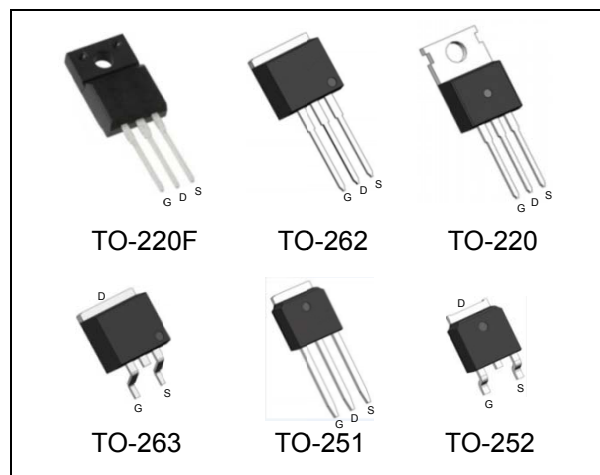
WMOS™ VD is Wayon's new high voltage power MOSFET family that is utilizing advanced technology for extremely low on-resistance and low gate charge performance. WMOS™ VD is suitable for applications which require superior power density and outstanding efficiency.

Features

- $V_{DS} = 650V @ T_{j,max}$
- $I_{DM} = 18A$
- Typ. $R_{DS(on)} = 0.6\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server



Absolute Maximum Ratings

Parameter	Symbol	WMK/WMM/WMO/WMP/WMN	WML	Unit
Drain-source voltage	V_{DSS}	600		V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$)	I_D	10		A
		5		A
($T_C = 100^\circ C$)				
Pulsed drain current ²⁾	I_{DM}	18		A
Gate-source voltage	V_{GS}	± 30		V
Avalanche energy, single pulse ³⁾	E_{AS}	55		mJ
Avalanche energy, repetitive ²⁾	E_{AR}	0.15		mJ
Avalanche current, repetitive ²⁾	I_{AR}	1.2		A
Power dissipation ($T_C = 25^\circ C$)	P_D	57	27	W
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		$^\circ C$
Continuous diode forward current	I_S	10		A
Diode pulse current	$I_{S,pulse}$	18		A

Thermal Characteristics

Parameter	Symbol	WMK/WMM/WMO/WMP/WMN	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	2.2	4.6	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =0.25 mA	600	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25mA	2.5	3.3	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =600 V, V _{GS} =0 V, T _J = 25°C T _J = 125°C	- -	- 10	1 -	μA
Gate leakage current, forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =1.5 A T _J = 25°C	- -	 0.6	 0.69	 Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	438	-	pF
Output capacitance	C _{OSS}		-	430	-	
Reverse transfer capacitance	C _{rss}		-	4.3	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 300V, I _D = 2A R _G = 25Ω, V _{GS} =10V	-	18	-	ns
Rise time	t _r		-	14	-	
Turn-off delay time	t _{d(off)}		-	47	-	
Fall time	t _f		-	10	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =480 V, I _D =2A, V _{GS} =0 to 10 V	-	2.3	-	nC
Gate to drain charge	Q _{gd}		-	8.0	-	
Gate charge total	Q _g		-	13.6	-	
Gate plateau voltage	V _{plateau}		-	5.3	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =1.5A	-	-	1.2	V
Reverse recovery time	t _{rr}	V _R =50 V, I _F =2A, dI _F /dt=100 A/μs	-	144	-	ns
Reverse recovery charge	Q _{rr}		-	0.83	-	μC
Peak reverse recovery current	I _{rrm}		-	12	-	A

Notes:

- Limited by $T_{j\max}$. Maximum duty cycle $D=0.5$.
- Repetitive rating: pulse width limited by maximum junction temperature.
- $I_{AS}=1.2\text{ A}$, $V_{DD}=50\text{ V}$, $R_G=25\Omega$, starting $T_j=25^\circ\text{C}$.

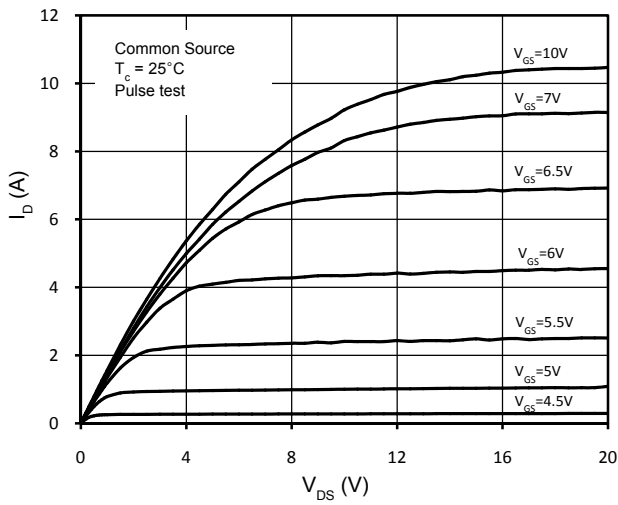


Figure 1. On-Region Characteristics

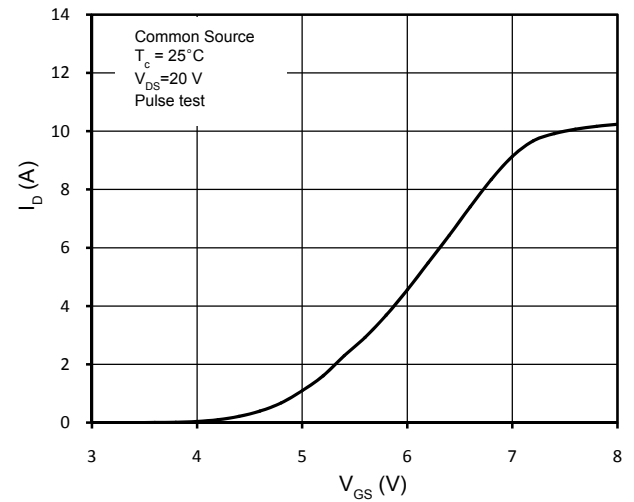


Figure 2. Transfer Characteristics

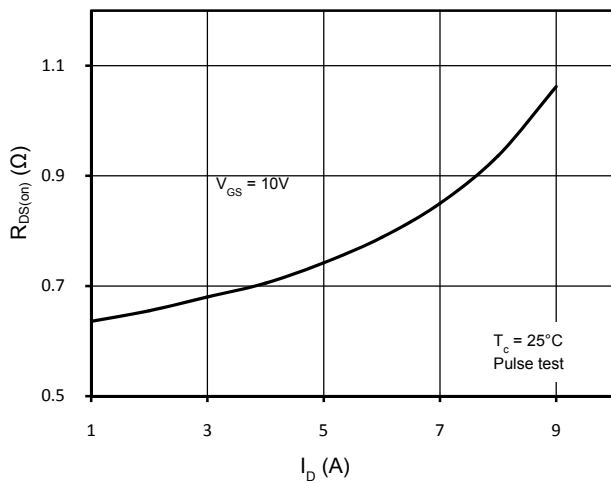


Figure 3. Static Drain-Source On Resistance

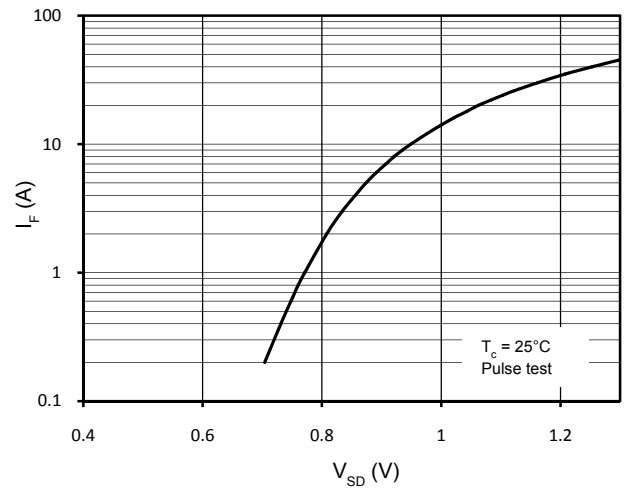
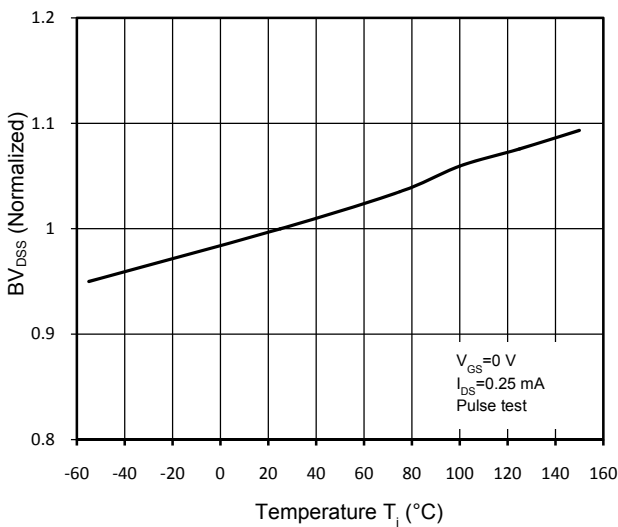
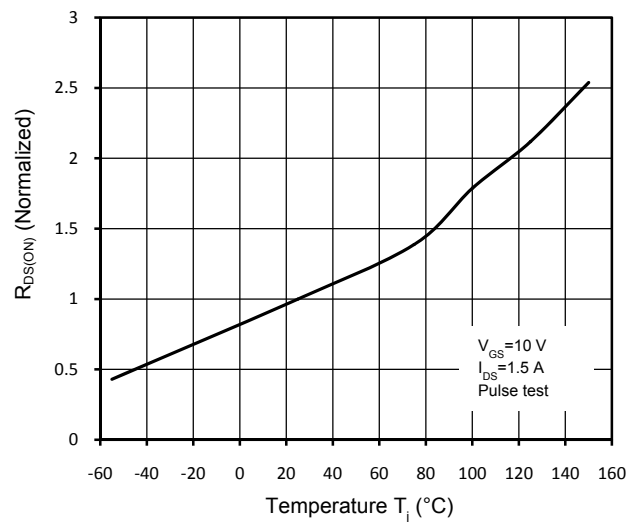


Figure 4. Body-Diode Forward Characteristics

Figure 5. Normalized BV_{DS} vs. TemperatureFigure 6. Normalized $R_{DS(on)}$ vs. Temperature

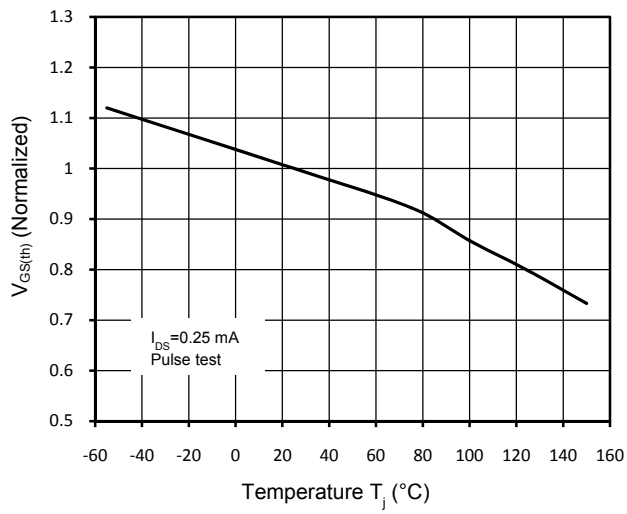


Figure 7. Threshold Voltage vs. Temperature

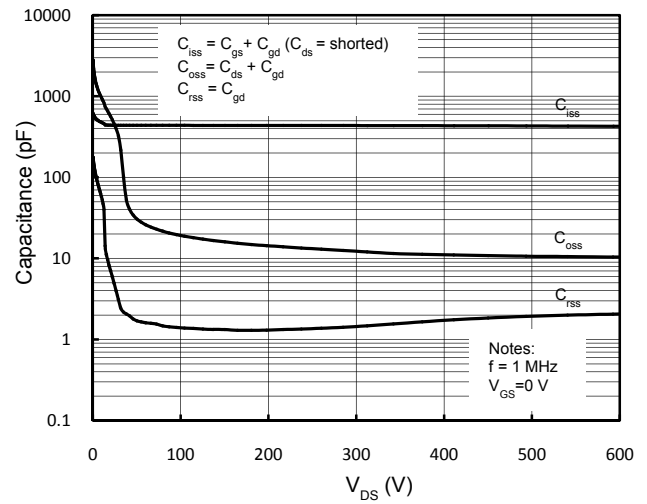


Figure 8. Capacitance Characteristics

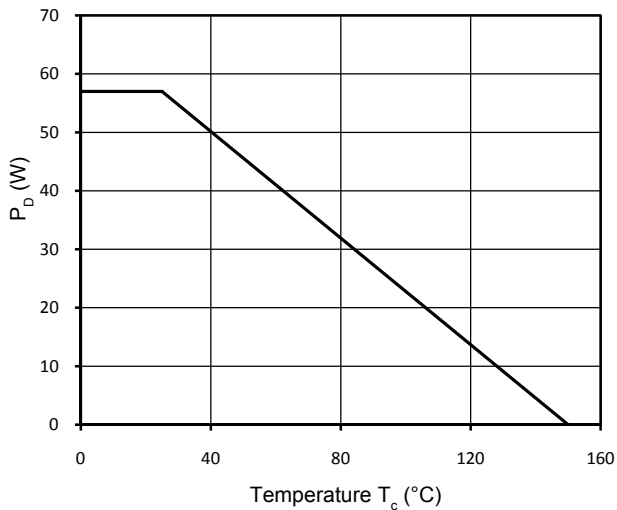


Figure 9. Power Dissipation

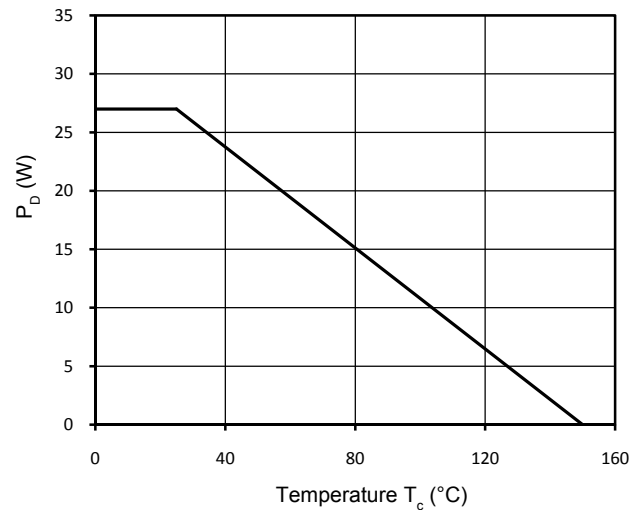


Figure 10. Power Dissipation (TO-220F)

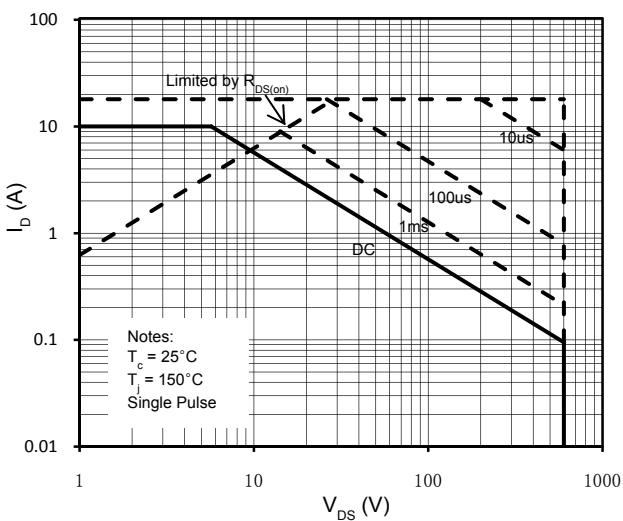


Figure 11. Maximum Safe Operating Area

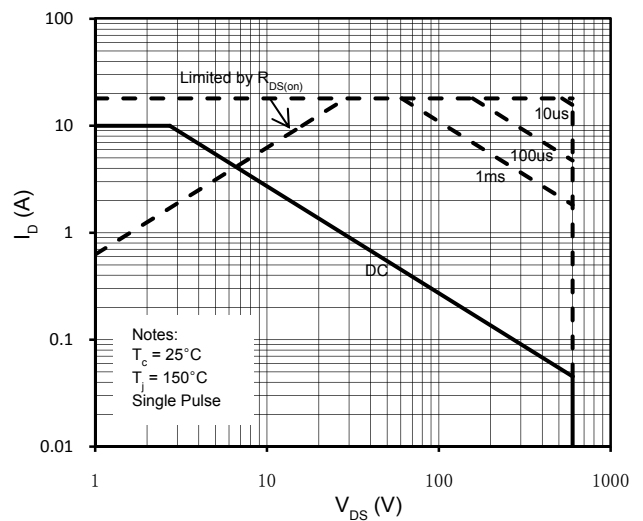


Figure 12. Maximum Safe Operating Area (TO-220F)

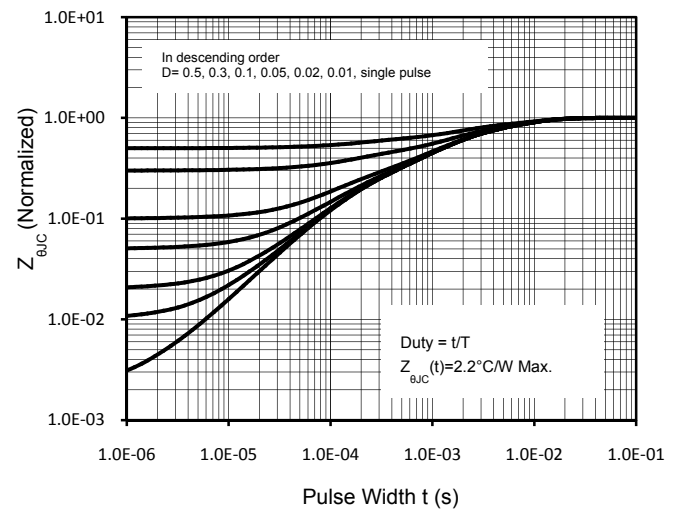
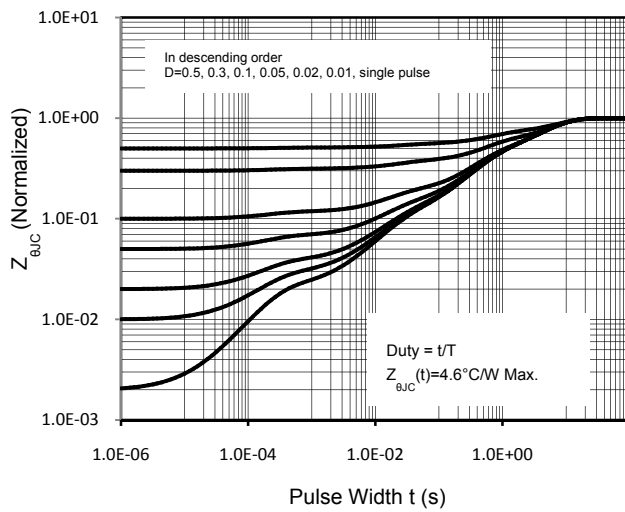


Figure 13. Transient Thermal Response Curve (TO-220F) Figure 14. Transient Thermal Response Curve

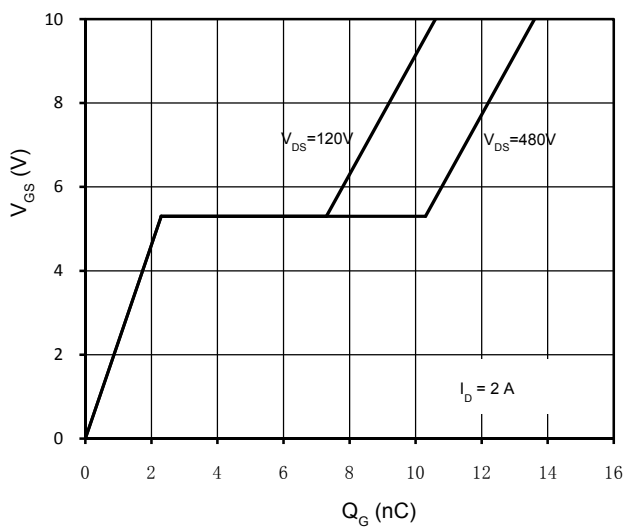
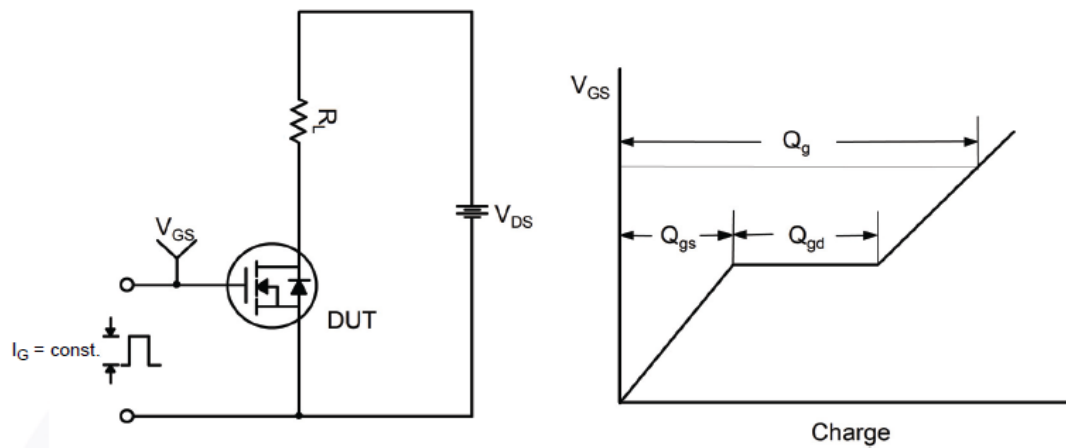
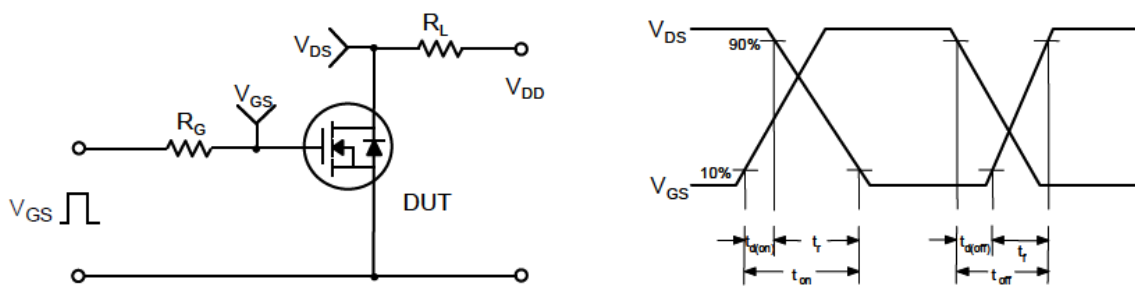


Figure 15. Gate Charge Characteristics

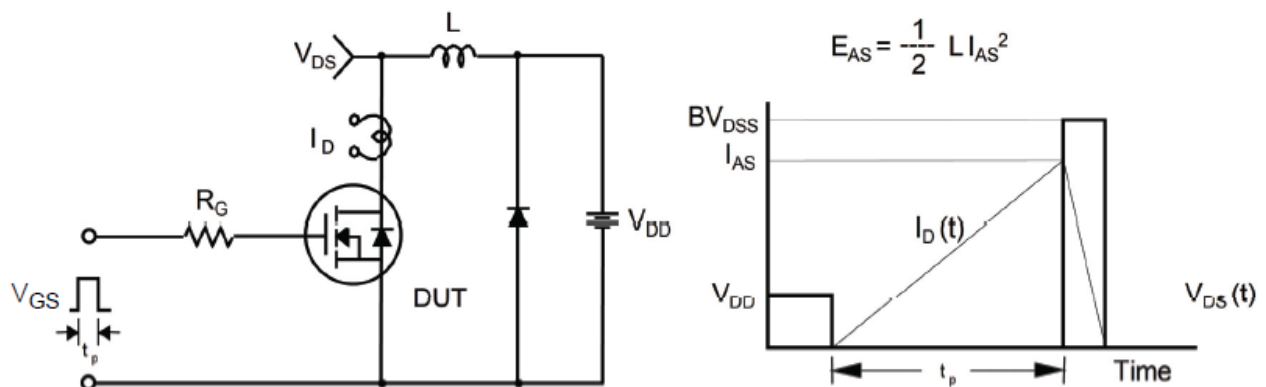
Gate Charge Test Circuit & Waveform

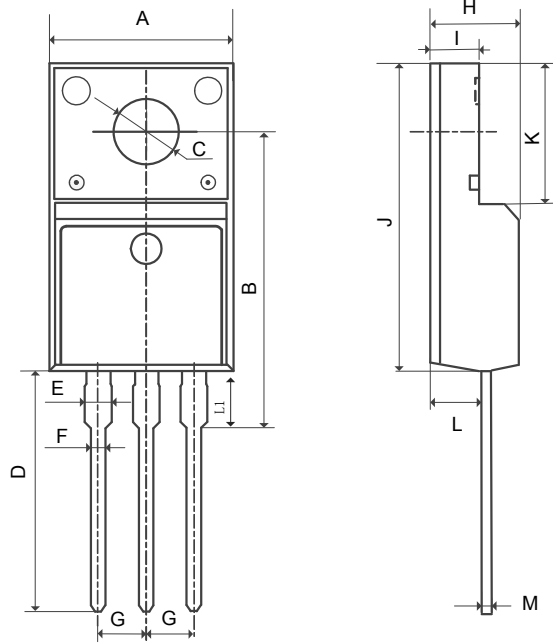


Switching Test Circuit & Waveforms

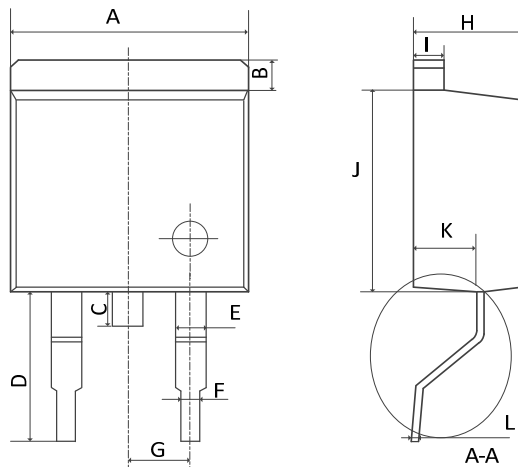


Unclamped Inductive Switching Test Circuit & Waveforms

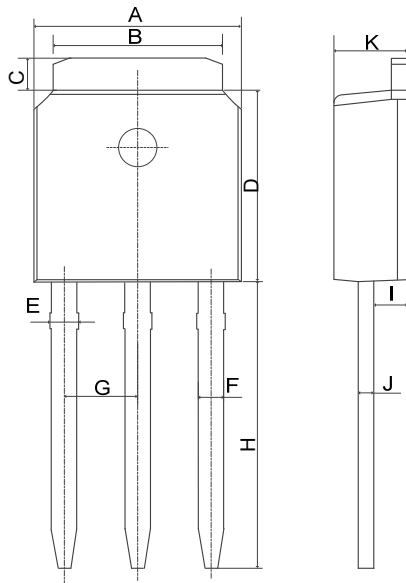


Mechanical Dimensions for TO-220F

COMMON DIMENSIONS

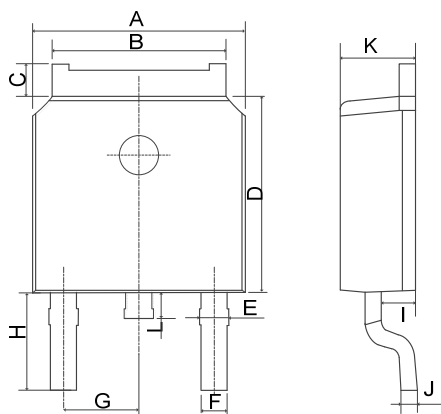
SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.10	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

Mechanical Dimensions for TO-263

COMMON DIMENSIONS

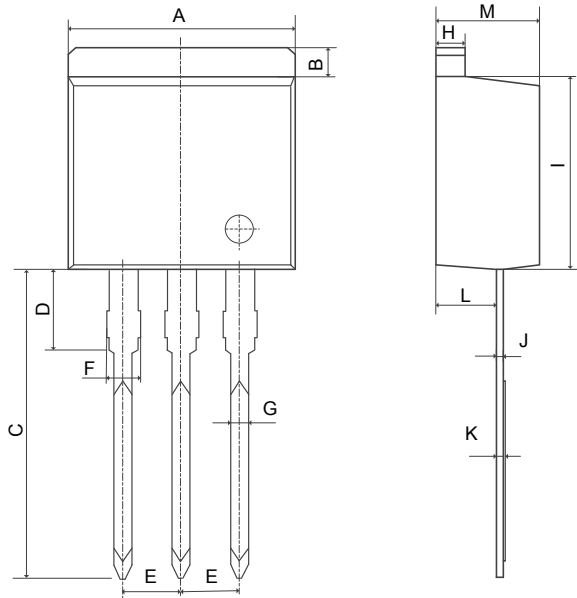
SYMBOL	MM	
	MIN	MAX
A	10.00	10.40
B	1.11	1.41
C	1.25	1.55
D	5.10	5.50
E	1.12	1.42
F	0.71	0.92
G	2.39	2.69
H	4.49	4.89
I	1.17	1.37
J	8.45	8.85
K	2.54	2.84
L	0.28	0.49

Mechanical Dimensions for TO-251

COMMON DIMENSIONS

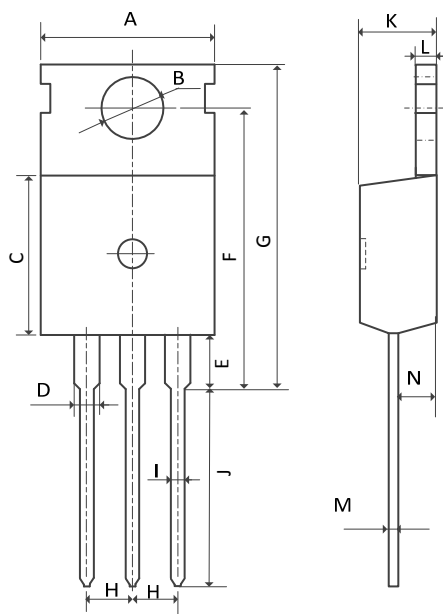
SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.46
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	9.00	9.65
I	0.90	1.17
J	0.40	0.61
K	2.10	2.50

Mechanical Dimensions for TO-252

COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

Mechanical Dimensions for TO-262

COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	10.00	10.40
B	1.11	1.41
C	13.56	14.16
D	3.58	3.98
E	2.39	2.69
F	1.07	1.47
G	0.71	0.92
H	1.17	1.37
I	8.45	8.85
J	0.28	0.49
K	0.32	0.52
L	2.54	2.85
M	4.50	4.90

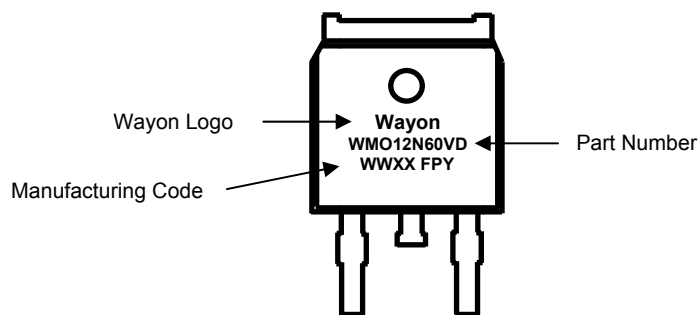
Mechanical Dimensions for TO-220

COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.20
B	3.40	3.80
C	8.90	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Ordering Information

Part	Package	Marking	Packing method
WML12N60VD	TO-220F	WML12N60VD	Tube
WMK12N60VD	TO-220	WMK12N60VD	Tube
WMN12N60VD	TO-262	WMN12N60VD	Tube
WMM12N60VD	TO-263	WMM12N60VD	Tape and Reel
WMO12N60VD	TO-252	WMO12N60VD	Tape and Reel
WMP12N60VD	TO-251	WMP12N60VD	Tube

Marking Information



Contact Information

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